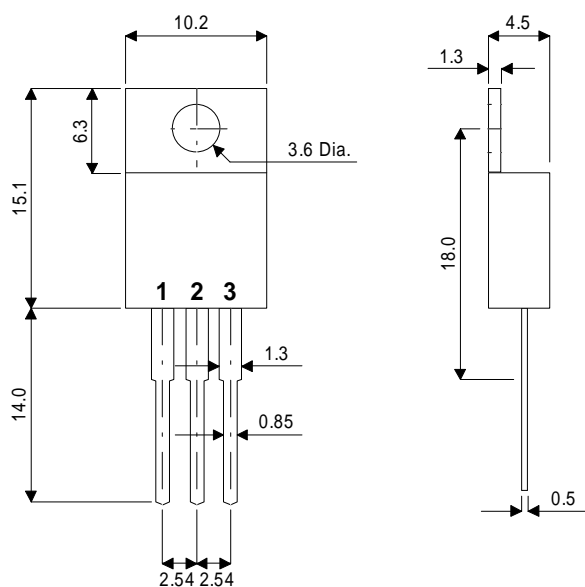


**MECHANICAL DATA**

Dimensions in mm



**TO220**

Pin 1 – Base      Pin 2 – Collector      Pin 3 – Emitter

**ADVANCED  
DISTRIBUTED BASE DESIGN  
HIGH VOLTAGE  
HIGH SPEED NPN  
SILICON POWER TRANSISTOR**

Designed for use in  
electronic ballast applications

- SEMEFAB DESIGNED AND DIFFUSED DIE
- HIGH VOLTAGE
- FAST SWITCHING
- HIGH ENERGY RATING
- MILITARY AND HI-REL VERSIONS  
AVAILABLE IN METAL AND CERAMIC  
SURFACE MOUNT PACKAGES

**FEATURES**

- Multi-base for efficient energy distribution across the chip resulting in significantly improved switching and energy ratings across full temperature range.
- Ion implant and high accuracy masking for tight control of characteristics from batch to batch.
- Triple Guard Rings for improved control of high voltages.

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$V_{CBO}$	Collector – Base Voltage	1000V
$V_{CEO}$	Collector – Emitter Voltage ( $I_B = 0$ )	500V
$V_{EBO}$	Emitter – Base Voltage ( $I_C = 0$ )	10V
$I_C$	Continuous Collector Current	4A
$I_{C(PK)}$	Peak Collector Current	7A
$I_B$	Base Current	2A
$P_{tot}$	Total Dissipation at $T_{case} = 25^{\circ}C$	65W
$T_{stg}$	Operating and Storage Temperature Range	-55 to +150°C

**ELECTRICAL CHARACTERISTICS** ( $T_{\text{case}} = 25^{\circ}\text{C}$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit		
<b>ELECTRICAL CHARACTERISTICS</b>							
$V_{\text{CEO(sus)}}$	Collector – Emitter Sustaining Voltage	$I_{\text{C}} = 10\text{mA}$	500		V		
$V_{\text{(BR)CBO}}$	Collector – Base Breakdown Voltage	$I_{\text{C}} = 1\text{mA}$	1000				
$V_{\text{(BR)EBO}}$	Emitter – Base Breakdown Voltage	$I_{\text{E}} = 1\text{mA}$	10				
$I_{\text{CBO}}$	Collector – Base Cut-Off Current	$V_{\text{CB}} = 1000\text{V}$		10	$\mu\text{A}$		
			$T_{\text{C}} = 125^{\circ}\text{C}$	100			
$I_{\text{CEO}}$	Collector – Emitter Cut-Off Current	$I_{\text{B}} = 0$	$V_{\text{CE}} = 500\text{V}$	100	$\mu\text{A}$		
$I_{\text{EBO}}$	Emitter Cut-Off Current	$V_{\text{EB}} = 9\text{V}$	$I_{\text{C}} = 0$		10		
				$T_{\text{C}} = 125^{\circ}\text{C}$	100		
$h_{\text{FE}}^*$	DC Current Gain	$I_{\text{C}} = 0.1\text{A}$	$V_{\text{CE}} = 5\text{V}$	20	40	—	
		$I_{\text{C}} = 0.5\text{A}$	$V_{\text{CE}} = 5\text{V}$	12	15		
		$I_{\text{C}} = 1\text{A}$	$V_{\text{CE}} = 1\text{V}$	5	8		
$V_{\text{CE(sat)}}^*$	Collector – Emitter Saturation Voltage	$I_{\text{C}} = 100\text{mA}$	$I_{\text{B}} = 20\text{mA}$		0.05	0.1	V
		$I_{\text{C}} = 0.5\text{A}$	$I_{\text{B}} = 0.1\text{A}$		0.15	0.2	
		$I_{\text{C}} = 1\text{A}$	$I_{\text{B}} = 0.2\text{A}$		0.3	0.5	
$V_{\text{BE(sat)}}^*$	Base – Emitter Saturation Voltage	$I_{\text{C}} = 0.5\text{A}$	$I_{\text{B}} = 0.1\text{A}$		0.8	1.0	V
		$I_{\text{C}} = 1\text{A}$	$I_{\text{B}} = 0.2\text{A}$		0.9	1.1	
<b>DYNAMIC CHARACTERISTICS</b>							
$f_{\text{t}}$	Transition Frequency	$I_{\text{C}} = 0.2\text{A}$	$V_{\text{CE}} = 4\text{V}$		20	MHz	
$C_{\text{ob}}$	Output Capacitance	$V_{\text{CB}} = 20\text{V}$	$f = 1\text{MHz}$		20	pF	

\* Pulse test  $t_{\text{p}} = 300\mu\text{s}$ ,  $\delta < 2\%$